

Using EMC's patented asymmetrical wrap geometry (U.S. Patent # 5,739,743), the thermal dissipation of the surface mount terminations is improved by increasing the solderable terminal area. This eliminates the need for bolt down heat sinks and tabs, reducing assembly costs.

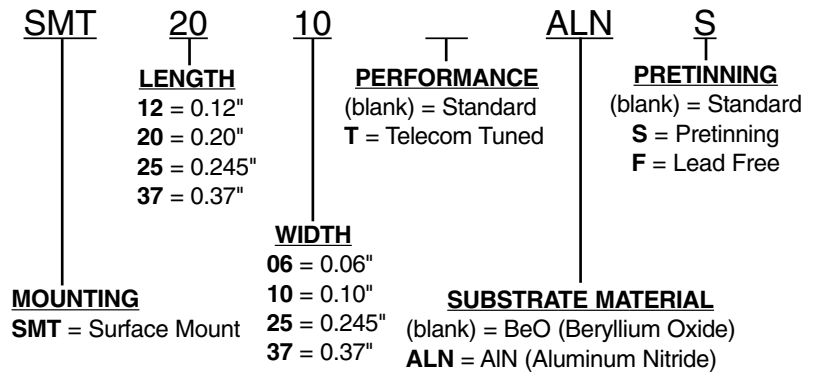
General Specifications

Nominal Impedance 50 Ohms \pm 5%
 Frequency Range DC to 2.7 GHz
 Power Rating 10 to 150 Watts
 Power Derating 100% @ 100° C
 Derates to 0% @ 150° C
 Operating Temperature -55° C to 150° C

Material Specifications

Substrates BeO or AlN
 Resistive Material Thick Film
 Termination Material Thick Film,
 Nickel Barrier, Solder Plated Finish

Ordering Information



Note: Not every combination of size is available.
 See selection table on page 37.
 Other ohms values available upon request. Please contact factory.



Selection Table

Power (W) Avg.	Substrate Type	Freq. (GHz)	Max. VSWR	Dimensions (inches)						Part Number
				L	W	T	TW	A	B	
10	AlN	2.0	1.25	0.120	0.060	0.026	0.054	0.025	0.025	SMT1206ALN
15	BeO	2.0	1.25	0.120	0.060	0.026	0.054	0.025	0.025	SMT1206
20	AlN	2.7	1.15	0.200	0.100	0.026	0.050	0.020	0.035	SMT2010TALN
20	AlN	2.0	1.25	0.200	0.100	0.041	0.090	0.020	0.035	SMT2010ALN
30	BeO	2.0	1.25	0.200	0.100	0.041	0.090	0.020	0.035	SMT2010
50	AlN	2.7	1.15	0.245	0.245	0.041	0.040	0.030	0.025	SMT2525TALN
60	AlN	2.0	1.25	0.245	0.245	0.041	0.120	0.030	0.025	SMT2525ALN
75	BeO	2.0	1.25	0.245	0.245	0.041	0.120	0.030	0.025	SMT2525
80	AlN	2.7	1.15	0.370	0.245	0.041	0.045	0.045	0.045	SMT3725TALN
80	AlN	2.0	1.25	0.370	0.245	0.041	0.120	0.045	0.045	SMT3725ALN
125	BeO	2.0	1.25	0.370	0.245	0.041	0.120	0.045	0.045	SMT3725
100	AlN	2.7	1.20	0.372	0.372	0.051	0.050	0.040	0.040	SMT3737TALN
100	AlN	2.0	1.35	0.372	0.372	0.051	0.175	0.040	0.040	SMT3737ALN
150	BeO	2.0	1.35	0.372	0.372	0.051	0.175	0.040	0.040	SMT3737

Dimensions

